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Substitute for form 1449B/PTO			Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT Date Submitted: February 5, 2002 (use as many sheets as necessary)			Application Number	Unassigned	
			Filing Date	02/05/2002	
			First Named Inventor	Igor KOUZNETSOV et al.	
			Group Art Unit	Unassigned	
			Examiner Name	Unassigned	
Sheet	1	of	7	Attorney Docket Number	035905-0118

10/066376
02/05/02

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
LP	A1	5,427,979		Chang	06/27/1995	
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	A3	4,498,226		Inoue et al.	02/12/1985	
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Examiner Signature	LONG PHAM	Date Considered	3/20/04
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LP	A69	JOHN H. DOUGLAS: "The Route to 3-D Chips," High Technology, September 1983, pgs. 55-59, Vol. 3, No. 9, High Technology Publishing Corporation, Boston, MA		
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LP	A71	O. BELLEZZA et al.: "A New Self-Aligned Field Oxide Cell for Multimegabit Eproms," IEDM, pgs. 579-582, IEEE	
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Examiner Signature	Long Pham	Date Considered	3/20/04
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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT Date Submitted: February 5, 2002 (use as many sheets as necessary)				Complete if Known	
				Application Number	Unassigned
				Filing Date	02/05/2002
				First Name of Inventor	Igor KOUZNETSOV et al.
				Group Art Unit	Unassigned
				Examiner Name	Unassigned
				Attorney Docket Number	035905-0118
Sheet	7	of	7		

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM- DD-YYYY	Pages, Column, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
LP	A123	5,383,149		Hong	01/17/1995	
	A124	5,572,046		Takemura	11/05/1996	
OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS						
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.				T ⁶
LP	A125	WEB PAGE-ime.org.sg; "Tachyon and IME to Build 3D Chips for Greater Speed and Performance," Press Release, dated January 18, 2002				
LP	A126	ICHIRO FUJIWARA et al.: "MONOS Memory Cell Scalable to 0.1µm and Beyond," pages 117-118				

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